SOT23 PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

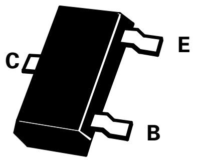
FMMTA55
FMMTA56

ISSUE 3 – JANUARY 1996 ✪

FEATURES

- Gain of 50 at I_C=100mA

PARTMARKING DETAIL - FMMTA55 - 2H
FMMTA56 - 2G
FMMTA55R - NB
FMMTA56R - MB



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FMMTA55	FMMTA56	UNIT
Collector-Base Voltage	V_{CBO}	-60	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	-80	V
Emitter-Base Voltage	V_{EBO}	-4		V
Continuous Collector Current	I_C	-500		mA
Power Dissipation at T_{amb}=25°C	P_{tot}	330		mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150		°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

		FMMTA55		FMMTA56			
PARAMETER	SYMBOL	MIN.	MAX.	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60		-80		V	I_C=-1mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-4		-4		V	I_E=-100μA, I_C=0
Collector-Emitter Cut-Off Current	I_{CES}		-0.1		-0.1	μA	V_{CE}=-60V
Collector-Base Cut-Off Current	I_{CBO}		 -0.1		-0.1	μA	V_{CB}=-80V, I_E=0 V_{CB}=-60V, I_E=0
Static Forward Current Transfer Ratio	h_{FE}	50 50		50 50			I_C=-10mA, V_{CE}=1V* I_C=-100mA, V_{CE}=1V*
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.25		-0.25	V	I_C=-100mA, I_B=-10mA*
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.2		-1.2	V	I_C=-100mA, V_{CE}=-1V*
Transition Frequency	f_T	100		100		MHz	I_C=-10mA, V_{CE}=-2V f=100MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%